



AOU414

N-Channel Enhancement Mode Field Effect Transistor

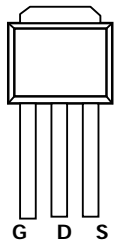
General Description

The AOU414 uses advanced trench technology to provide excellent $R_{DS(ON)}$, shoot-through immunity and body diode characteristics. This device is ideally suited for use as a low side switch in CPU core power conversion. *Standard Product AOU414 is Pb-free (meets ROHS & Sony 259 specifications). AOU414L is a Green Product ordering option. AOU414 and AOU414L are electrically identical.*

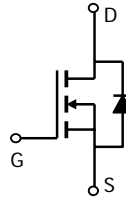
Features

V_{DS} (V) = 30V
 I_D = 85A (V_{GS} = 10V)
 $R_{DS(ON)}$ < 5.7m Ω (V_{GS} = 10V)
 $R_{DS(ON)}$ < 7.5m Ω (V_{GS} = 4.5V)

TO-251



Top View
 Drain
 Connected to
 Tab



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ^{B,G}	I_D	$T_C=25^\circ\text{C}$ ^G	A
		$T_C=100^\circ\text{C}$ ^B	
Pulsed Drain Current	I_{DM}	200	
Avalanche Current ^C	I_{AR}	30	A
Repetitive avalanche energy $L=0.1\text{mH}$ ^C	E_{AR}	140	mJ
Power Dissipation ^B	P_D	$T_C=25^\circ\text{C}$	W
		$T_C=100^\circ\text{C}$	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 175	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	100	125	$^\circ\text{C/W}$
Maximum Junction-to-Lead ^C				

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V	30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =24V, V _{GS} =0V T _J =55°C		0.005	1	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} = ±20V			100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} I _D =250μA	1.2	1.8	2.4	V
I _{D(ON)}	On state drain current	V _{GS} =10V, V _{DS} =5V	200			A
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =20A T _J =125°C		4.7	5.7	mΩ
		V _{GS} =4.5V, I _D =20A		6	7.5	mΩ
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =20A		85		S
V _{SD}	Diode Forward Voltage	I _S =1A, V _{GS} =0V		0.7	1	V
I _S	Maximum Body-Diode Continuous Current				85	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =15V, f=1MHz		6060	7000	pF
C _{oss}	Output Capacitance			638		pF
C _{rss}	Reverse Transfer Capacitance			355		pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz		0.45	0.6	Ω
SWITCHING PARAMETERS						
Q _{g(10V)}	Total Gate Charge	V _{GS} =4.5V, V _{DS} =15V, I _D =20A		96.4	115	nC
Q _{g(4.5V)}	Total Gate Charge			46.4	55	nC
Q _{gs}	Gate Source Charge			13.6		nC
Q _{gd}	Gate Drain Charge			15.6		nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =10V, V _{DS} =15V, R _L =0.75Ω, R _{GEN} =3Ω		15.7	21	ns
t _r	Turn-On Rise Time			14.2	21	ns
t _{D(off)}	Turn-Off DelayTime			55.5	75	ns
t _f	Turn-Off Fall Time			14	21	ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =20A, dI/dt=100A/μs		31	38	ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =20A, dI/dt=100A/μs		24	29	nC

A: The value of R_{θJA} is measured with the device in a still air environment with T_A=25°C.

B: The power dissipation P_D is based on T_{J(MAX)}=175°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C: Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=175°C.

D: The R_{θJA} is the sum of the thermal impedance from junction to case R_{θJC} and case to ambient.

E: The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

F: These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_{J(MAX)}=175°C.

G: The maximum current rating is limited by bond-wires.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

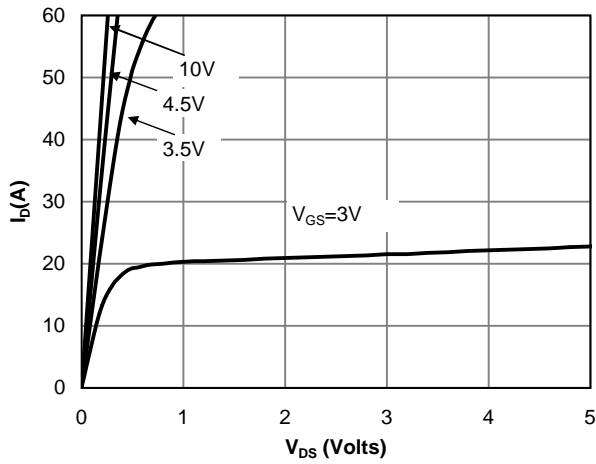


Figure 1: On-Region Characteristics

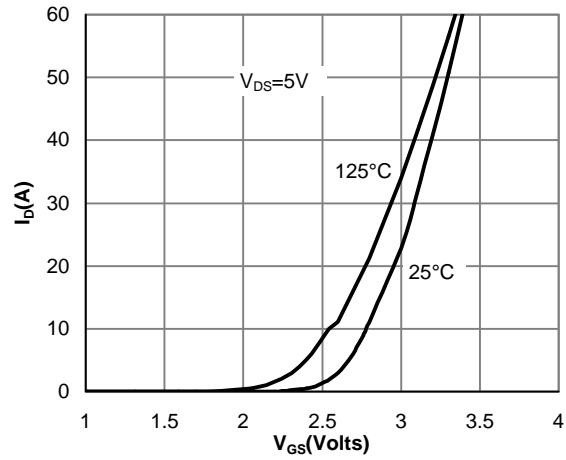


Figure 2: Transfer Characteristics

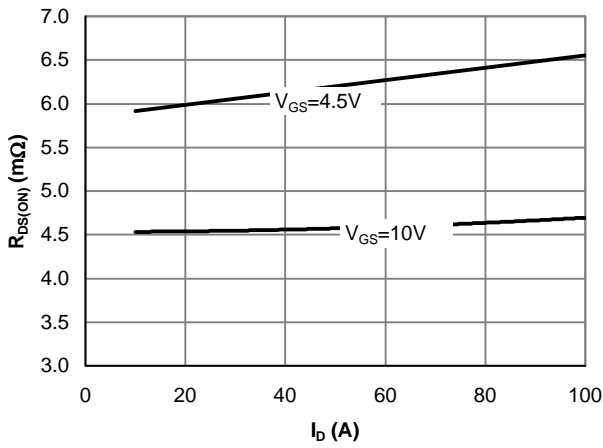


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

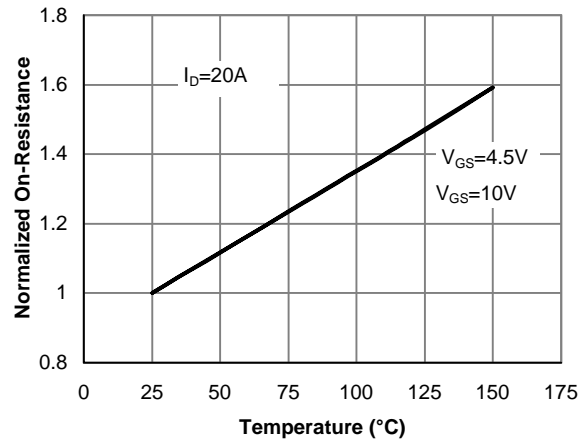


Figure 4: On-Resistance vs. Junction Temperature

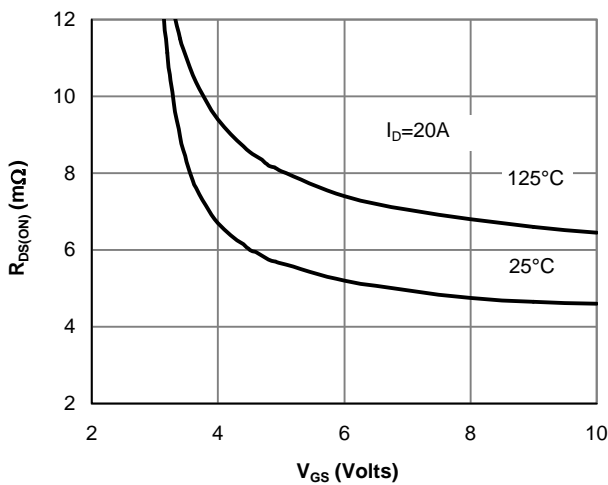


Figure 5: On-Resistance vs. Gate-Source Voltage

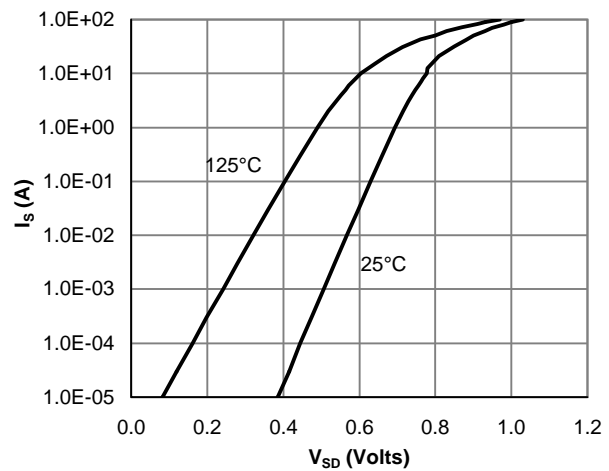


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

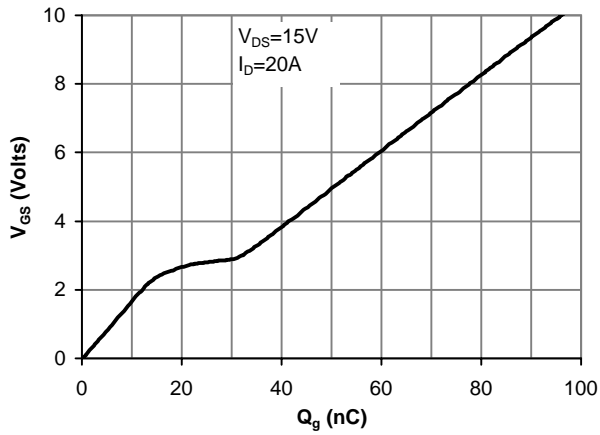


Figure 7: Gate-Charge Characteristics

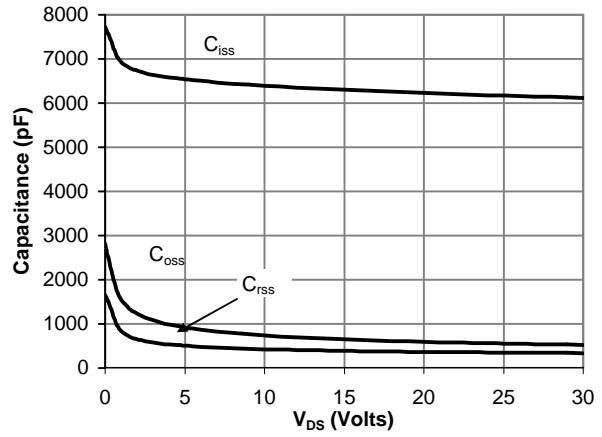


Figure 8: Capacitance Characteristics

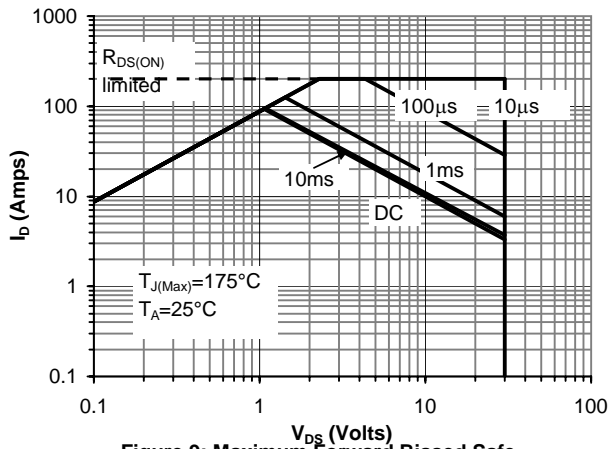


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

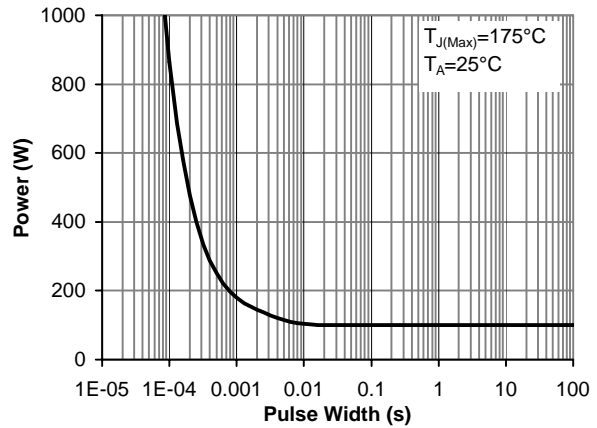


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)

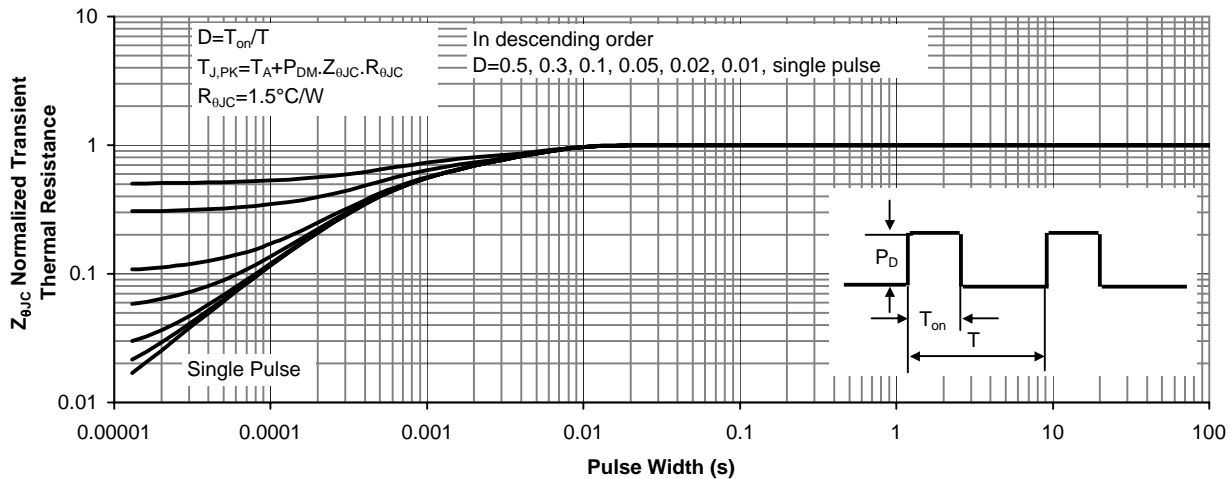


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

